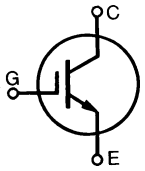
IXYS

HiPerFAST™ IGBT

IXGH 20N60B
IXGT 20N60B

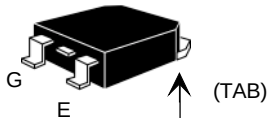
V_{CES} = 600 V
I_{C25} = 40 A
$V_{CE(sat)typ}$ = 1.7 V
$t_{fi(typ)}$ = 100 ns

Preliminary data sheet

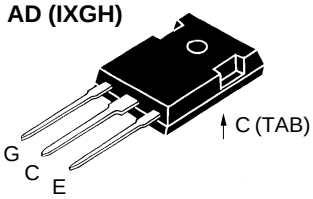


Symbol	Test Conditions	Maximum Ratings	
V_{CES}	T_J = 25°C to 150°C	600	V
V_{CGR}	T_J = 25°C to 150°C; R_{GE} = 1 MΩ	600	V
V_{GES}	Continuous	±20	V
V_{GEM}	Transient	±30	V
I_{C25}	T_C = 25°C	40	A
I_{C90}	T_C = 90°C	20	A
I_{CM}	T_C = 25°C, 1 ms	80	A
SSOA (RBSOA)	V_{GE}= 15 V, T_{VJ} = 125°C, R_G = 22 Ω Clamped inductive load, L = 100 μH	I_{CM} = 40 @ 0.8 V_{CES}	A
P_C	T_C = 25°C	150	W
T_J		-55 ... +150	°C
T_{JM}		150	°C
T_{stg}		-55 ... +150	°C
Maximum Lead and Tab temperature for soldering 1.6 mm (0.062 in.) from case for 10 s		300	°C
M_d	Mounting torque, TO-247 AD	1.13/10	Nm/lb.in.
Weight	TO-247	6	g
	TO-268	4	g

TO-268 (D3) (IXGT)



TO-247 AD (IXGH)



G = Gate, C = Collector,
E = Emitter, TAB = Collector

Features
- International standard packages JEDEC TO-268 surface mountable and JEDEC TO-247 AD
- High current handling capability
- Latest generation HDMOS™ process
- MOS Gate turn-on
  - drive simplicity

Applications
- AC motor speed control
- DC servo and robot drives
- DC choppers
- Uninterruptible power supplies (UPS)
- Switched-mode and resonant-mode power supplies

Advantages
- Space savings (two devices in one package)
- High power density
- Suitable for surface mounting
- Switching speed for high frequency applications
- Easy to mount with 1 screw,TO-247 (isolated mounting screw hole)

Symbol	Test Conditions		Characteristic Values (T_J = 25°C, unless otherwise specified) min.	typ.	max.	
BV_{CES}	I_C = 250μA, V_{GE} = 0 V		600			V
$V_{GE(th)}$	I_C = 250 μA, V_{CE} = V_{GE}		2.5		5.0	V
I_{CES}	V_{CE} = 0.8 • V_{CES}	T_J = 25°C			200	μA
	V_{GE} = 0 V	T_J = 125°C			1	mA
I_{GES}	V_{CE} = 0 V, V_{GE} = ±20 V				±100	nA
$V_{CE(sat)}$	I_C = I_{C90}, V_{GE} = 15 V			1.7	2.0	V

IXYS reserves the right to change limits, test conditions, and dimensions.

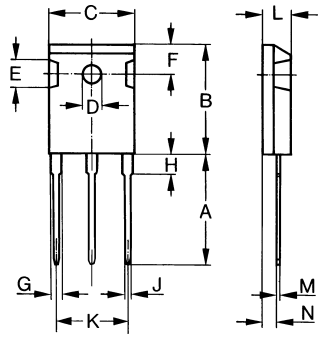
96533B (7/99)

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Symbol	Test Conditions	Characteristic Values (T_J = 25°C, unless otherwise specified) min.	typ.	max.	
g_{fs}	$I_C = I_{C90}$; V_{CE} = 10 V, Pulse test, t ≤ 300 µs, duty cycle ≤ 2 %	9	17		S
C_{ies}	V_{CE} = 25 V, V_{GE} = 0 V, f = 1 MHz		1500		pF
C_{oes}			175		pF
C_{res}			40		pF
Q_g	$I_C = I_{C90}$, V_{GE} = 15 V, V_{CE} = 0.5 V_{CES}		90		nC
Q_{ge}			11		nC
Q_{gc}			30		nC
$t_{d(on)}$	**Inductive load, T_J = 25°C**		15		ns
t_{ri}	$I_C = I_{C90}$, V_{GE} = 15 V, L = 100 µH,		35		ns
E_{on}	V_{CE} = 0.8 V_{CES}, $R_G = R_{off}$ = 10 Ω		0.15		mJ
$t_{d(off)}$			150	200	ns
t_{fi}			100	150	ns
E_{off}	Note 1		0.7	1.0	mJ
$t_{d(on)}$	**Inductive load, T_J = 125°C**		15		ns
t_{ri}	$I_C = I_{C90}$, V_{GE} = 15 V, L = 100 µH		35		ns
E_{on}	V_{CE} = 0.8 V_{CES}, $R_G = R_{off}$ = 10 Ω		0.15		mJ
$t_{d(off)}$			220		ns
t_{fi}			140		ns
E_{off}	Note 1		1.2		mJ
R_{thJC}				0.83	K/W
R_{thCK}			0.25		K/W

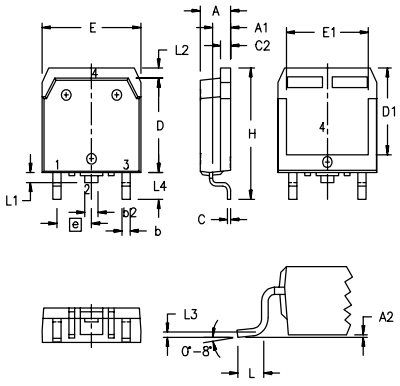
Note 1: Switching times may increase for V_{CE} (Clamp) > 0.8 • V_{CES}, higher T_J or increased R_G

TO-247 AD (IXGH) Outline



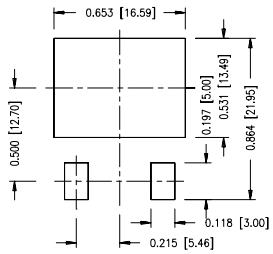
Dim.	Millimeter Min.	Max.	Inches Min.	Max.
A	19.81	20.32	0.780	0.800
B	20.80	21.46	0.819	0.845
C	15.75	16.26	0.610	0.640
D	3.55	3.65	0.140	0.144
E	4.32	5.49	0.170	0.216
F	5.4	6.2	0.212	0.244
G	1.65	2.13	0.065	0.084
H	-	4.5	-	0.177
J	1.0	1.4	0.040	0.055
K	10.8	11.0	0.426	0.433
L	4.7	5.3	0.185	0.209
M	0.4	0.8	0.016	0.031
N	1.5	2.49	0.087	0.102

TO-268AA (D^3 PAK)



Dim.	Millimeter Min.	Max.	Inches Min.	Max.
A	4.9	5.1	.193	.201
A_1	2.7	2.9	.106	.114
A_2	.02	.25	.001	.010
b	1.15	1.45	.045	.057
b_2	1.9	2.1	.75	.83
C	.4	.65	.016	.026
D	13.80	14.00	.543	.551
E	15.85	16.05	.624	.632
E_1	13.3	13.6	.524	.535
e	5.45 BSC		.215 BSC	
H	18.70	19.10	.736	.752
L	2.40	2.70	.094	.106
L1	1.20	1.40	.047	.055
L2	1.00	1.15	.039	.045
L3	0.25 BSC		.010 BSC	
L4	3.80	4.10	.150	.161

Min. Recommended Footprint



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IXYS MOSFETS and IGBTs are covered by one or more of the following U.S. patents:
4,835,592 4,881,106 5,017,508 5,049,961 5,187,117 5,486,715
4,850,072 4,931,844 5,034,796 5,063,307 5,237,481 5,381,025

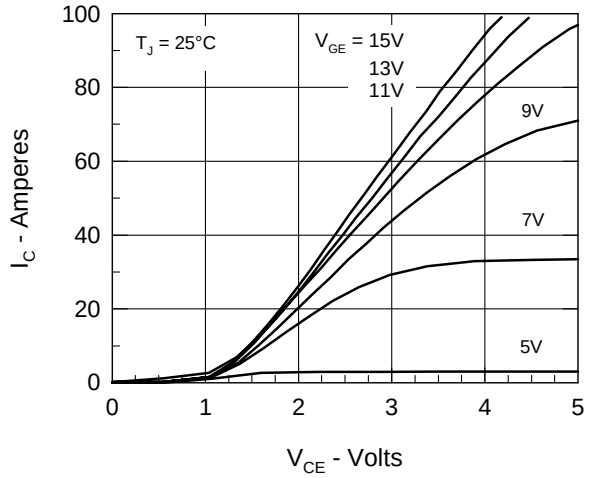


Fig. 1. Output Characteristics

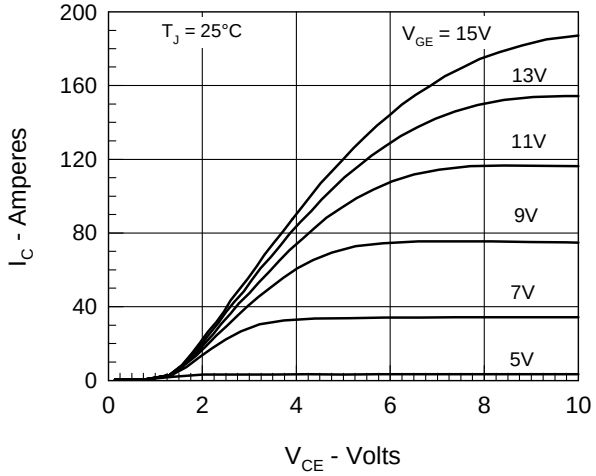


Fig. 2. Extended Output Characteristics

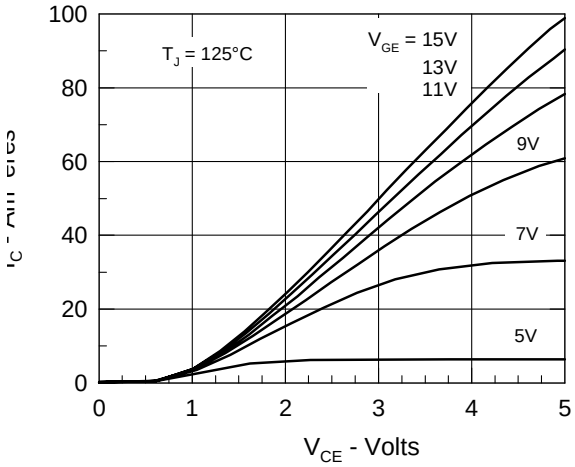


Fig. 3. High Temperature Output Characteristics

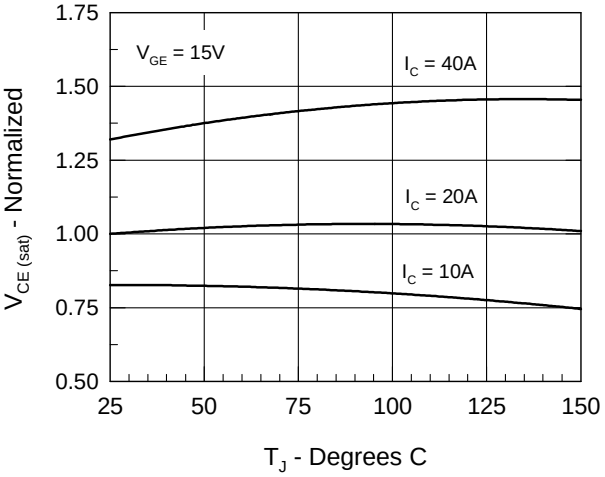


Fig. 4. Temperature Dependence of $V_{CE(sat)}$

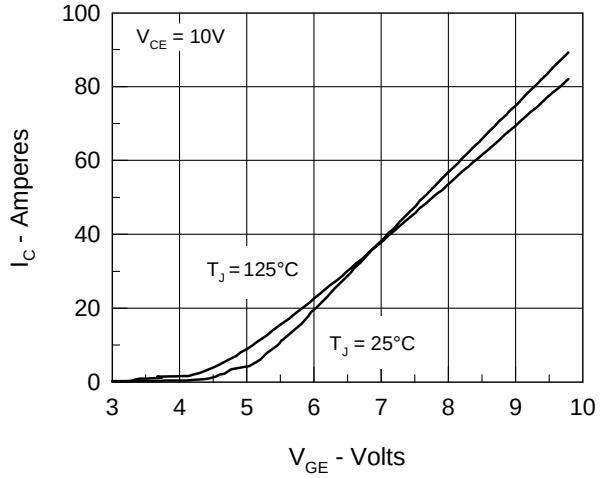


Fig. 5. Admittance Curves

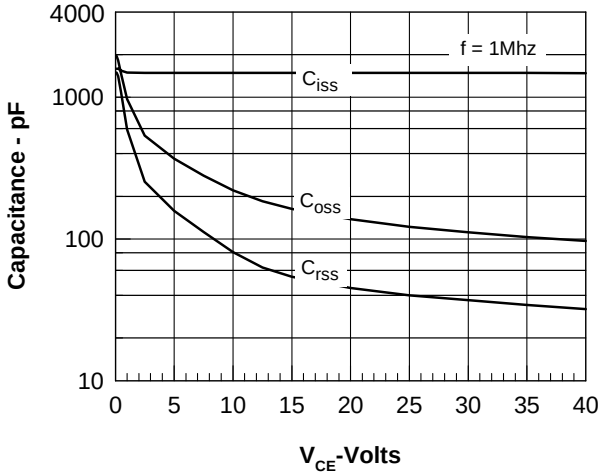


Fig. 6. Capacitance Curves

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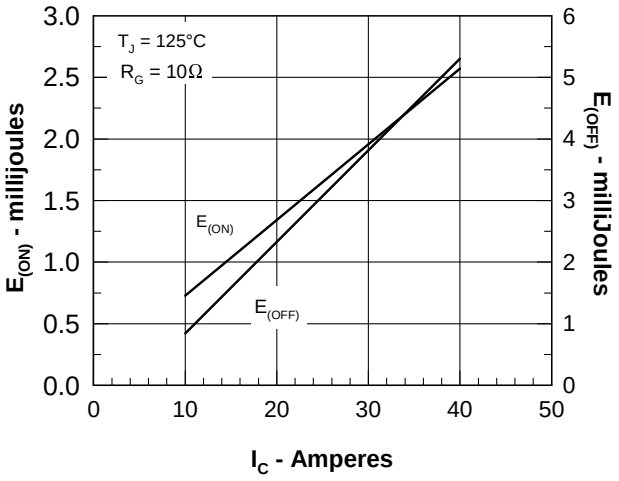


Fig. 7. Dependence of E_{ON} and E_{OFF} on I_C.

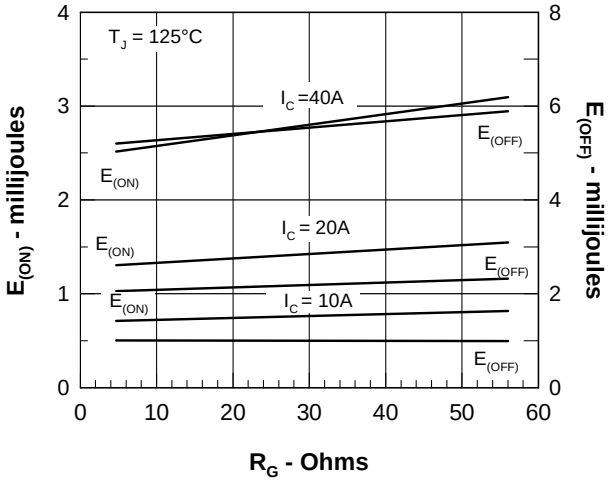


Fig. 8. Dependence of E_{ON} and E_{OFF} on R_G.

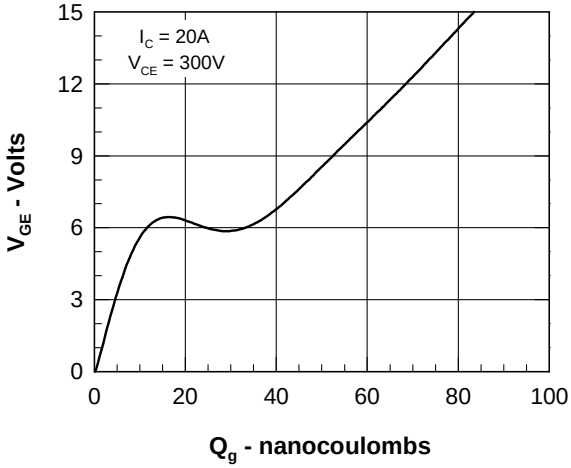


Fig. 9. Gate Charge

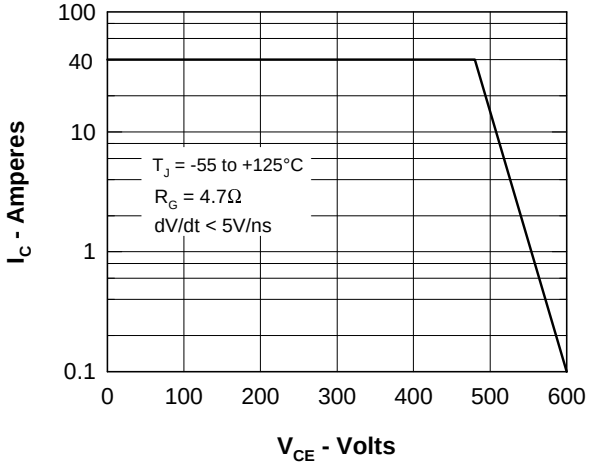


Fig. 10. Turn-off Safe Operating Area

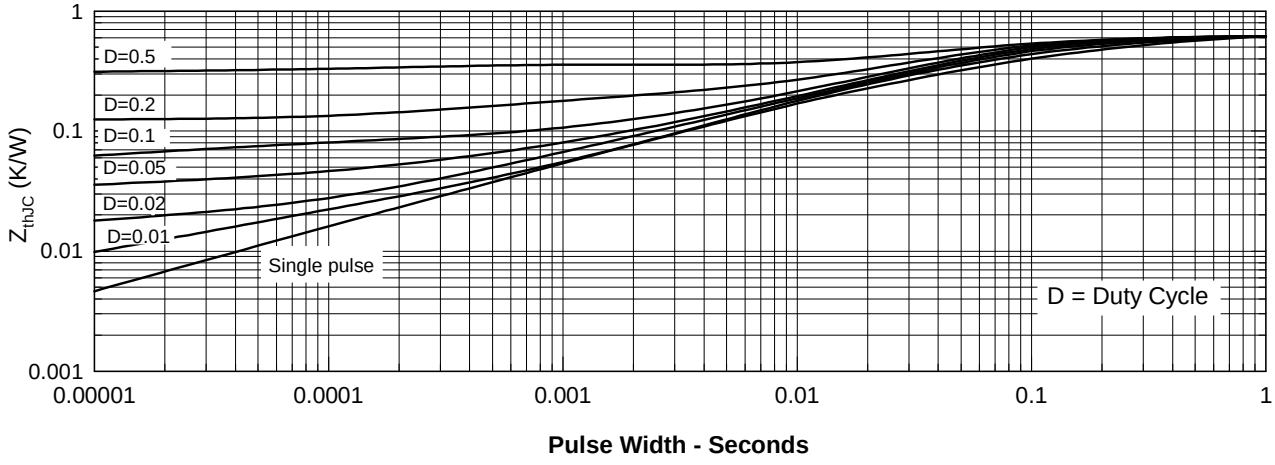


Fig. 11. IGBT Transient Thermal Resistance Junction-to-Case

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